# 2SB0621

### Silicon PNP epitaxial planar type

For low-frequency driver amplification Complementary to SD0592

#### Features

- $\bullet$  Low collector-emitter saturation voltage  $V_{\mbox{CE(sat)}}$
- $\bullet$  High transition frequency  $f_{T}$

### Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-30	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-25	V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	-5	V	
Collector current	I <sub>C</sub>	-1	А	
Peak collector current	I <sub>CP</sub> -1.5		А	
Collector power dissipation	P <sub>C</sub>	750	mW	
Junction temperature	Tj	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	

Package

#### • Code

- TO-92B-B1
- Pin Name
  - 1. Emitter
  - 2. Collector
  - 3. Base

#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = -10 \ \mu {\rm A}, I_{\rm E} = 0$	-30			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -2  {\rm mA}, I_{\rm B} = 0$	-25			V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_{\rm E} = -10 \mu {\rm A}, I_{\rm C} = 0$	-5			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -20 \text{ V}, I_E = 0$			- 0.1	μΑ
	h <sub>FE1</sub> *	$V_{CE} = -10 \text{ V}, I_C = -500 \text{ mA}$	85		340	
Forward current transfer ratio	h <sub>FE2</sub>	$V_{CE} = -5 V, I_C = -1 A$	50			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -500 \text{ mA}, I_{\rm B} = -50 \text{ mA}$		- 0.2	- 0.4	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_{\rm C} = -500 \text{ mA}, I_{\rm B} = -50 \text{ mA}$		- 0.85	-1.2	V
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		20	30	pF

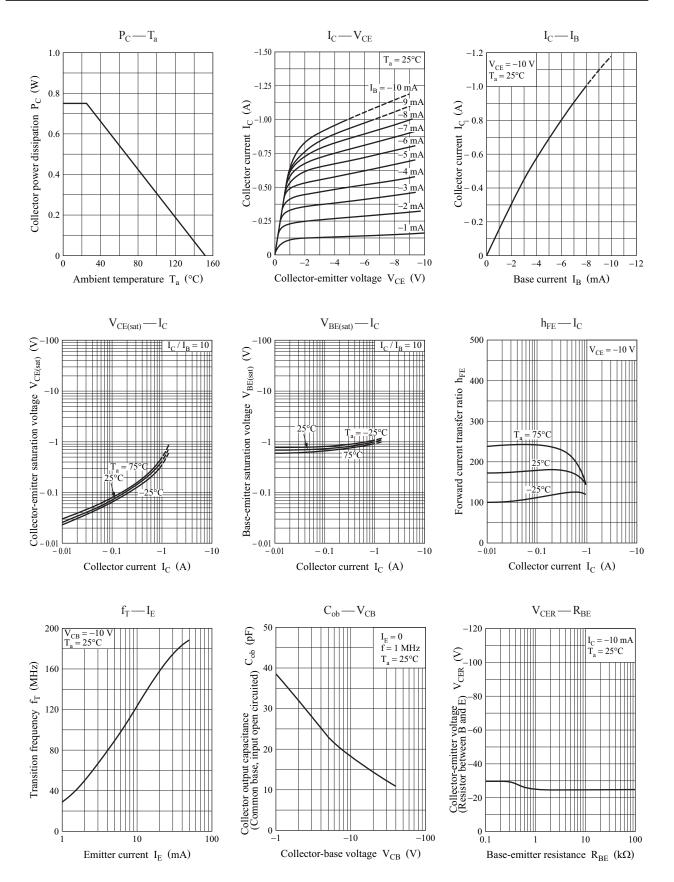
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Rank classification

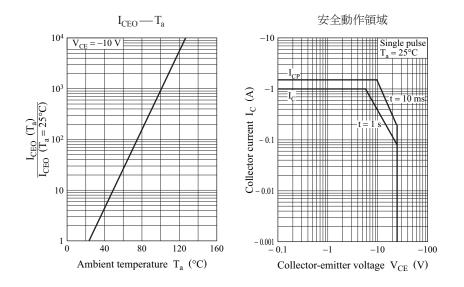
Rank	Q	R	S
$h_{\rm FE1}$	85 to 170	120 to 240	170 to 340

#### 2SB0621

### Panasonic



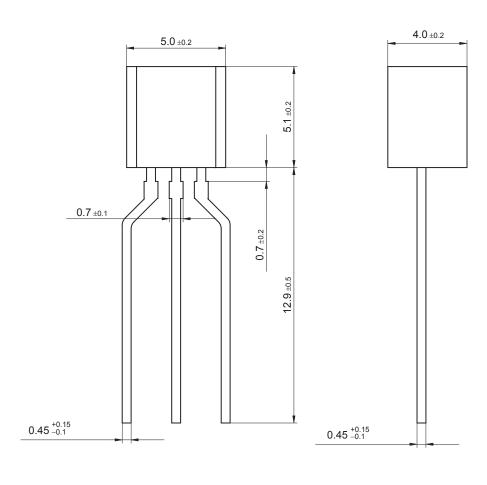
# **Panasonic**

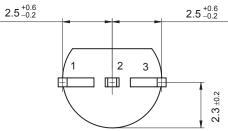


## Panasonic

TO-92-B1

Unit: mm





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